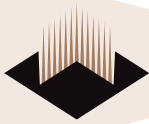


WHITE ELECTRONIC DESIGNS

512MB – 2x32Mx64 DDR SDRAM UNBUFFERED, w/PLL

FEATURES

- DDR200, DDR266 and DDR333
  - JEDEC design specifications
- Double-data-rate architecture
- Bi-directional data strobes (DQS)
- Differential clock inputs (CK & CK#)
- Programmable Read Latency 2,2.5 (clock)
- Programmable Burst Length (2,4,8)
- Programmable Burst type (sequential & interleave)
- Edge aligned data output, center aligned data input
- Auto and self refresh
- Serial presence detect
- Dual Rank
- Power supply: 2.5V ± 0.20V
- JEDEC standard 200 pin SO-DIMM package
  - Package height options:
    AD4: 35.5mm (1.38")
    BD4: 31.75mm (1.25")

NOTE: Consult factory for availability of:
- RoHS compliant products
- Vendor source control options
- Industrial temperature option

DESCRIPTION

The W3EG6466S is a 2x32Mx64 Double Data Rate SDRAM memory module based on 512Mb DDR SDRAM components. The module consists of sixteen 32Mx8 components as eight 64Mx8 stacked DDR SDRAMs in 66 pin TSOP packages mounted on a 200 pin FR4 substrate.

Synchronous design allows precise cycle control with the use of system clock. Data I/O transactions are possible on both edges and Burst Lengths allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

* This product is under development, is not qualified or characterized and is subject to change without notice.

www.DataSheet4U.com

OPERATING FREQUENCIES

	DDR333 @CL=2.5	DDR266 @CL=2	DDR266 @CL=2.5	DDR200 @CL=2
Clock Speed	166MHz	133MHz	133MHz	100MHz
CL-t_{RCD}-t_{RP}	2.5-3-3	2-2-2	2.5-3-3	2-2-2

White Electronic Designs Corp. reserves the right to change products or specifications without notice.

PIN CONFIGURATION

Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol
1	VREF	51	VSS	101	A9	151	DQ42
2	VREF	52	VSS	102	A8	152	DQ46
3	VSS	53	DQ19	103	VSS	153	DQ43
4	VSS	54	DQ23	104	VSS	154	DQ47
5	DQ0	55	DQ24	105	A7	155	VCC
6	DQ4	56	DQ28	106	A6	156	VCC
7	DQ1	57	VCC	107	A5	157	VCC
8	DQ5	58	VCC	108	A4	158	NC
9	VCC	59	DQ25	109	A3	159	VSS
10	VCC	60	DQ29	110	A2	160	NC
11	DQS0	61	DQS3	111	A1	161	VSS
12	DQM0	62	DQM3	112	A0	162	VSS
13	DQ2	63	VSS	113	VCC	163	DQ48
14	DQ6	64	VSS	114	VCC	164	DQ52
15	VSS	65	DQ26	115	A10/AP	165	DQ49
16	VSS	66	DQ30	116	BA1	166	DQ53
17	DQ3	67	DQ27	117	BA0	167	VCC
18	DQ7	68	DQ31	118	RAS#	168	VCC
19	DQ8	69	VCC	119	WE#	169	DQS6
20	DQ12	70	VCC	120	CAS#	170	DQM6
21	VCC	71	NC	121	CS0#	171	DQ50
22	VCC	72	NC	122	CS1#	172	DQ54
23	DQ9	73	NC	123	NC	173	VSS
24	DQ13	74	NC	124	NC	174	VSS
25	DQS1	75	VSS	125	VSS	175	DQ51
26	DQM1	76	VSS	126	VSS	176	DQ55
27	VSS	77	DQS8	127	DQ32	177	DQ56
28	VSS	78	DQM8	128	DQ36	178	DQ60
29	DQ10	79	NC	129	DQ33	179	VCC
30	DQ14	80	NC	130	DQ37	180	VCC
31	DQ11	81	VCC	131	VCC	181	DQ57
32	DQ15	82	VCC	132	VCC	182	DQ61
33	VCC	83	NC	133	DQS4	183	DQS7
34	VCC	84	NC	134	DQM4	184	DQM7
35	CK0	85	NC	135	DQ34	185	VSS
36	VCC	86	NC	136	DQ38	186	VSS
37	CK0#	87	VSS	137	VSS	187	DQ58
38	VSS	88	VSS	138	VSS	188	DQ62
39	VSS	89	NC	139	DQ35	189	DQ59
40	VSS	90	VSS	140	DQ39	190	DQ63
41	DQ16	91	NC	141	DQ40	191	VCC
42	DQ20	92	VCC	142	DQ44	192	VCC
43	DQ17	93	VCC	143	VCC	193	SDA
44	DQ21	94	VCC	144	VCC	194	SA0
45	VCC	95	CKE1	145	DQ41	195	SCL
46	VCC	96	CKE0	146	DQ45	196	SA1
47	DQS2	97	NC	147	DQS5	197	VCCSPD
48	DQM2	98	NC	148	DQM5	198	SA2
49	DQ18	99	A12	149	VSS	199	VCCID
50	DQ22	100	A11	150	VSS	200	NC

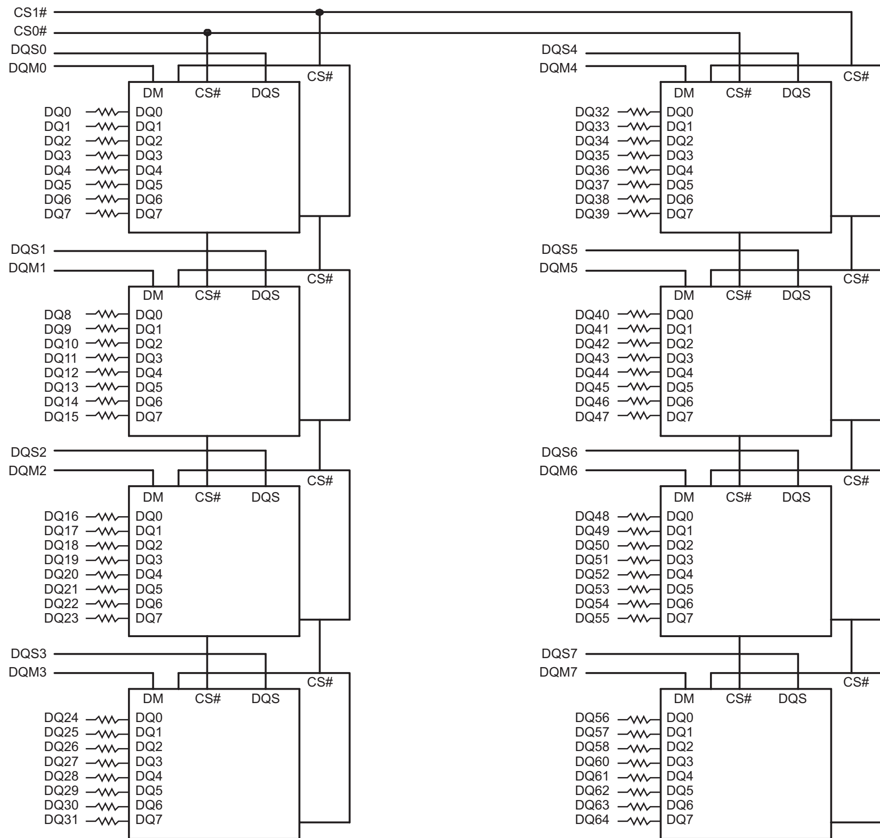
PIN NAMES

A0 – A12	Accress input (Multiplexed)
BA0-BA1	Bank Select Accress
DQ0-DQ63	Data Input/Output
DQS0-DQS7	Data Strobe Input/Output
CK0	Clock Input
CK0#	Clock input
CKE0-CKE1	Clock Enable input
CS0#-CS1#	Chip select Input
RAS#	Row Accress Strobe
CAS#	Column Accress Strobe
WE#	Write Enable
DQM0-DQM7	Data-In Mask
VCC	Power Supply
VSS	Ground
VREF	Power Supply for Reference
VCCSPD	Serial EEPROM Power Supply
SDA	Serial data I/O
SCL	Serial clock
SA0-SA2	Accress in EEPROM
VCCID	VCC Identification Flag
NC	No Connect

* Not Used

White Electronic Designs Corp. reserves the right to change products or specifications without notice.

FUNCTIONAL BLOCK DIAGRAM



RAS# → RAS: DDR SDRAMs

CAS# → CAS: DDR SDRAMs

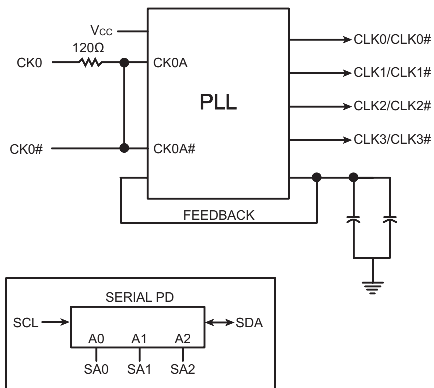
BA0-BA1 → BA0-BA1: DDR SDRAMs

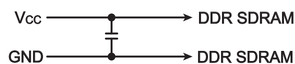
WE# → WE: DDR SDRAMs

A0-A12 → A0-A12: DDR SDRAMs

CKE0 → CKE0: DDR SDRAMs

CKE1 → CKE1: DDR SDRAMs





NOTE: All datalines are terminated through a 22 ohm series resistor.

White Electronic Designs Corp. reserves the right to change products or specifications without notice.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Voltage on any pin relative to V_{SS}	V_{IN}, V_{OUT}	-0.5 to 3.6	V
Voltage on V_{CC} supply relative to V_{SS}	V_{CC}, V_{CCQ}	-1.0 to 3.6	V
Storage Temperature	T_{STG}	-55 to +150	°C
Power Dissipation	P_D	16	W
Short Circuit Current	I_{OS}	50	mA

Note:

Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded.
Functional operation should be restricted to recommended operating condition.
Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

DC CHARACTERISTICS

$0°C \leq T_A \leq 70°C$, $V_{CC} = 2.5V \pm 0.2V$

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	2.3	2.7	V
Supply Voltage	V_{CCQ}	2.3	2.7	V
Reference Voltage	V_{REF}	$V_{CCQ/2}$ - 50mV	$V_{CCQ/2}$ + 50mV	V
Termination Voltage	V_{TT}	V_{REF} - 0.04	V_{REF} + 0.04	V
Input High Voltage	V_{IH}	V_{REF} + 0.15	V_{CCQ} + 0.3	V
Input Low Voltage	V_{IL}	-0.3	V_{REF} - 0.15	V
Output High Voltage	V_{OH}	V_{TT} + 0.76	—	V
Output Low Voltage	V_{OL}	—	V_{TT} - 0.76	V

CAPACITANCE

$T_A = 25°C$, f = 1MHz, $V_{CC} = 3.3V$, V_{REF} =1.4V ± 200mV

Parameter	Symbol	Max	Unit
Input Capacitance (A0-A12)	C_{IN1}	50	pF
Input Capacitance (RAS#, CAS#, WE#)	C_{IN2}	50	pF
Input Capacitance (CKE0, CKE1)	C_{IN3}	26	pF
Input Capacitance (CK0,CK0#)	C_{IN4}	5.5	pF
Input Capacitance (CS0#, CS1#)	C_{IN5}	26	pF
Input Capacitance (DQM0-DQM8)	C_{IN6}	13	pF
Input Capacitance (BA0-BA1)	C_{IN7}	50	pF
Data input/output capacitance (DQ0-DQ63)(DQS)	C_{OUT}	13	pF

I_{DD} SPECIFICATIONS AND TEST CONDITIONS

$0°C \leq T_A \leq 70°C$, V_{CCQ} = 2.5V ±0.2V, V_{CC} = 2.5V ±0.2V

			DDR333@CL=2.5	DDR266@CL=2, 2.5	DDR200@CL=2	
Parameter	Symbol	Conditions	Max	Max	Max	Units
Operating Current	I_{DD0}	One device bank; Active - Precharge; t_{RC}=t_{RC}(MIN); t_{CK}=t_{CK}(MIN); DQ,DM and DQS inputs changing once per clock cycle; Address and control inputs changing once every two cycles.	1600	1440	1360	mA
Operating Current	I_{DD1}	One device bank; Active-Read-Precharge; Burst = 2; t_{RC}=t_{RC}(MIN);t_{CK}=t_{CK}(MIN); Iout = 0mA; Address and control inputs changing once per clock cycle.	1800	1640	1560	mA
Precharge Power-Down Standby Current	I_{DD2P}	All device banks idle; Power- down mode; t_{CK}=t_{CK}(MIN); CKE=(low)	48	48	48	mA
Idle Standby Current	I_{DD2F}	CS# = High; All device banks idle; t_{CK}=t_{CK}(MIN); CKE = high; Address and other control inputs changing once per clock cycle. Vin = Vref for DQ, DQS and DM.	400	320	320	mA
Active Power-Down Standby Current	I_{DD3P}	One device bank active; Power-down mode; t_{CK}(MIN); CKE=(low)	560	480	480	mA
Active Standby Current	I_{DD3N}	CS# = High; CKE = High; One device bank; Active-Precharge; t_{RC}=t_{RAS}(MAX); t_{CK}=t_{CK}(MIN); DQ, DM and DQS inputs changing twice per clock cycle; Address and other control inputs changing once per clock cycle.	880	720	720	mA
Operating Current	I_{DD4R}	Burst = 2; Reads; Continous burst; One device bank active;Address and control inputs changing once per clock cycle; t_{CK}=t_{CK}(MIN); Iout = 0mA.	2160	1840	1840	mA
Operating Current	I_{DD4W}	Burst = 2; Writes; Continous burst; One device bank active; Address and control inputs changing once per clock cycle; t_{CK}=t_{CK}(MIN); DQ,DM and DQS inputs changing twice per clock cycle.	2160	1800	1800	mA
Auto Refresh Current	I_{DD5}	t_{RC}=t_{RC}(MIN)	2240	2000	2000	mA
Self Refresh Current	I_{DD6}	CKE $\leq$ 0.2V	48	48	48	mA
Operating Current	I_{DD7A}	Four bank interleaving Reads (BL=4) with auto precharge with t_{RC}=t_{RC} (MIN); t_{CK}=t_{CK}(MIN); Address and control inputs change only during Active Read or Write commands.	3120	2960	2720	mA

* For DDR333 consult factory

DETAILED TEST CONDITIONS FOR DDR SDRAM I_{DD1} & I_{DD7A}

I_{DD1} : OPERATING CURRENT : ONE BANK

1. Typical Case : V_{CC}=2.5V, T=25°C
2. Worst Case : V_{CC}=2.7V, T=10°C
3. Only one bank is accessed with t_{RC} (min), Burst Mode, Address and Control inputs on NOP edge are changing once per clock cycle. I_{OUT} = 0mA
4. Timing Patterns :
   - DDR200 (100 MHz, CL=2) : t_{CK}=10ns, CL2, BL=4, t_{RCD}=2*t_{CK}, t_{RAS}=5*t_{CK}
     Read : A0 N R0 N N P0 N A0 N - repeat the same timing with random address changing; 50% of data changing at every burst
   - DDR266 (133MHz, CL=2.5) : t_{CK}=7.5ns, CL=2.5, BL=4, t_{RCD}=3*t_{CK}, t_{RC}=9*t_{CK}, t_{RAS}=5*t_{CK}
     Read : A0 N N R0 N P0 N N N A0 N - repeat the same timing with random address changing; 50% of data changing at every burst
   - DDR266 (133MHz, CL=2) : t_{CK}=7.5ns, CL=2, BL=4, t_{RCD}=3*t_{CK}, t_{RC}=9*t_{CK}, t_{RAS}=5*t_{CK}
     Read : A0 N N R0 N P0 N N N A0 N - repeat the same timing with random address changing; 50% of data changing at every burst
   - DDR333 (166MHz, CL=2.5) : t_{CK}=6ns, BL=4, t_{RCD}=10*t_{CK}, t_{RAS}=7*t_{CK}
     Read : A0 N N R0 N P0 N N N A0 N - repeat the same timing with random address changing; 50% of data changing at every burst

I_{DD7A} : OPERATING CURRENT : FOUR BANKS

1. Typical Case : V_{CC}=2.5V, T=25°C
2. Worst Case : V_{CC}=2.7V, T=10°C
3. Four banks are being interleaved with t_{RC} (min), Burst Mode, Address and Control inputs on NOP edge are not changing. Iout=0mA
4. Timing Patterns :
   - DDR200 (100 MHz, CL=2) : t_{CK}=10ns, CL2, BL=4, t_{RRD}=2*t_{CK}, t_{RCD}=3*t_{CK}, Read with Autoprecharge
     Read : A0 N A1 R0 A2 R1 A3 R2 A0 R3 A1 R0 - repeat the same timing with random address changing; 100% of data changing at every burst
   - DDR266 (133MHz, CL=2.5) : t_{CK}=7.5ns, CL=2.5, BL=4, t_{RRD}=3*t_{CK}, t_{RCD}=3*t_{CK}
     Read with Autoprecharge
     Read : A0 N A1 R0 A2 R1 A3 R2 N R3 A0 N A1 R0 - repeat the same timing with random address changing; 100% of data changing at every burst
   - DDR266 (133MHz, CL=2) : t_{CK}=7.5ns, CL2=2, BL=4, t_{RRD}=2*t_{CK}, t_{RCD}=2*t_{CK}
     Read : A0 N A1 R0 A2 R1 A3 R2 N R3 A0 N A1 R0 - repeat the same timing with random address changing; 100% of data changing at every burst
   - DDR333 (166MHz, CL=2.5) : t_{CK}=6ns, BL=4, t_{RRD}=3*t_{CK}, t_{RCD}=3*t_{CK}, Read with Autoprecharge
     Read : A0 N A1 R0 A2 R1 A3 R2 N R3 A0 N A1 R0 - repeat the same timing with random address changing; 100% of data changing at every burst

Legend : A = Activate, R = Read, W = Write, P = Precharge, N = NOP

A (0-3) = Activate Bank 0-3
R (0-3) = Read Bank 0-3

White Electronic Designs Corp. reserves the right to change products or specifications without notice.

DDR SDRAM COMPONENT ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

AC CHARACTERISTICS		335		262		265/202		UNITS	NOTES
PARAMETER	**SYMBOL**	**MIN**	**MAX**	**MIN**	**MAX**	**MIN**	**MAX**		
Access window of DQs from CK/CK#	t_{AC}	-0.70	+0.70	-0.75	+0.75	-0.75	+0.75	ns	
CK high-level width	t_{CH}	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}	26
CK low-level width	t_{CL}	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}	26
Clock cycle time, CL = 2.5	$t_{CK\ (2.5)}$	6	13	7.5	13	7.5	13	ns	39, 44
Clock cycle time, CL = 2	$t_{CK\ (2)}$	7.5	13	7.5	13	7.5/10	13	ns	39, 44
DQ and DM input hold time relative to DQS	t_{DH}	0.45		0.5		0.5		ns	23, 27
DQ and DM input setup time relative to DQS	t_{DS}	0.45		0.5		0.5		ns	23, 27
DQ and DM input pulse width (for each input)	t_{DIPW}	1.75		1.75		1.75		ns	27
Access window of DQS from CK/CK#	t_{DQSCK}	-0.60	+0.60	-0.75	+0.75	-0.75	+0.75	ns	
DQS input high pulse width	t_{DQSH}	0.35		0.35		0.35		t_{CK}	
DQS input low pulse width	t_{DQSL}	0.35		0.35		0.35		t_{CK}	
DQS-DQ skew, DQS to last DQ valid, per group, per access	t_{DQSQ}		0.4		0.5		0.5	ns	22, 23
Write command to first DQS latching transition	t_{DQSS}	0.75	1.25	0.75	1.25	0.75	1.25	t_{CK}	
DQS falling edge to CK rising - setup time	t_{DSS}	0.20		0.20		0.20		t_{CK}	
DQS falling edge from CK rising - hold time	t_{DSH}	0.20		0.20		0.20		t_{CK}	
Half clock period	t_{HP}	t_{CH},t_{CL}		t_{CH},t_{CL}		t_{CH},t_{CL}		ns	8
Data-out high-impedance window from CK/CK#	t_{HZ}		+0.70		+0.75		+0.75	ns	16, 36
Data-out low-impedance window from CK/CK#	t_{LZ}	-0.70		-0.75		-0.75		ns	16, 36
Address and control input hold time (fast slew rate)	t_{IHF}	0.75		0.90		0.90		ns	12
Address and control input setup time (fast slew rate)	t_{ISF}	0.75		0.90		.900		ns	12
Address and control input hold time (slow slew rate)	t_{IHS}	0.8		1		1		ns	12
Address and control input setup time (slow slew rate)	t_{ISS}	0.8		1		1		ns	12
Address and Control input pulse width (for each input)	t_{IPW}	2.2		2.2		2.2		ns	
LOAD MODE REGISTER command cycle time	t_{MRD}	12		15		15		ns	

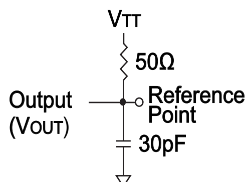
DDR SDRAM COMPONENT ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS (Continued)

AC CHARACTERISTICS		335		262		265/202		UNITS	NOTES
PARAMETER	SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX		
DQ-DQS hold, DQS to first DQ to go non-valid, per access	t_{QH}	t_{HP} - t_{QHS}		t_{HP} - t_{QHS}		t_{HP} - t_{QHS}		ns	22, 23
Data hold skew factor	t_{QHS}		0.75		0.75		0.75	ns	
ACTIVE to PRECHARGE command	t_{RAS}	42	70,000	40	120,000	40	120,000	ns	31, 47
ACTIVE to READ with Auto precharge command	t_{RAP}	15		15		20		ns	
ACTIVE to ACTIVE/AUTO REFRESH command period	t_{RC}	60		60		65		ns	
AUTO REFRESH command period	t_{RFC}	72		75		75		ns	42
ACTIVE to READ or WRITE delay	t_{RCD}	15		15		20		ns	
PRECHARGE command period	t_{RP}	15		15		20		ns	
DQS read preamble	t_{RPRE}	0.9	1.1	0.9	1.1	0.9	1.1	t_{CK}	37
DQS read postamble	t_{RPST}	0.4	0.6	0.4	0.6	0.4	0.6	t_{CK}	37
ACTIVE bank a to ACTIVE bank b command	t_{RRD}	12		15		15		ns	
DQS write preamble	t_{WPRE}	0.25		0.25		0.25		t_{CK}	
DQS write preamble setup time	t_{WPRES}	0		0		0		ns	18, 19
DQS write postamble	t_{WPST}	0.4	0.6	0.4	0.6	0.4	0.6	t_{CK}	17
Write recovery time	t_{WR}	15		15		15		ns	
Internal WRITE to READ command delay	t_{WTR}	1		1		1		t_{CK}	
Data valid output window	NA	t_{QH} - t_{DQSQ}		t_{QH} - t_{DQSQ}		t_{QH} - t_{DQSQ}		ns	22
REFRESH to REFRESH command interval	t_{REFC}		70.3		70.3		70.3	μs	21
Average periodic refresh interval	t_{REFI}		7.8		7.8		7.8	μs	21
Terminating voltage delay to VDD	t_{VTD}	0		0		0		ns	
Exit SELF REFRESH to non-READ command	t_{XSNR}	75		75		75		ns	
Exit SELF REFRESH to READ command	t_{XSRD}	200		200		200		t_{CK}	

White Electronic Designs Corp. reserves the right to change products or specifications without notice.

Notes

1. All voltages referenced to V_{SS}.
2. Tests for AC timing, I_{DD}, and electrical AC and DC characteristics may be conducted at nominal reference/supply voltage levels, but the related specifications and device operation are guaranteed for the full voltage range specified.
3. Outputs measured with equivalent load:



4. AC timing and I_{DD} tests may use a V_{IL}-to-V_{IH} swing of up to 1.5V in the test environment, but input timing is still referenced to V_{REF} (or to the crossing point for CK/CK#), and parameter specifications are guaranteed for the specified AC input levels under normal use conditions. The mini-mum slew rate for the input signals used to test the device is 1V/ns in the range between V_{IL}(AC) and V_{IH}(AC).
5. The AC and DC input level specifications are as defined in the SSTL_2 Standard (i.e., the receiver will effectively switch as a result of the signal crossing the AC input level, and will remain in that state as long as the signal does not ring back above [below] the DC input LOW [HIGH] level).
6. V_{REF} is expected to equal $V_{CCQ/2}$ of the transmitting device and to track variations in the DC level of the same. Peak-to-peak noise (non-common mode) on V_{REF} may not exceed ±2 percent of the DC value. Thus, from $V_{CCQ/2}$, V_{REF} is allowed ±25mV for DC error and an additional ±25mV for AC noise. This measurement is to be taken at the nearest V_{REF} bypass capacitor.
7. V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors, is expected to be set equal to V_{REF} and must track variations in the DC level of V_{REF}.
8. I_{DD} is dependent on output loading and cycle rates. Specified values are obtained with mini-mum cycle time at CL = 2 for 262, 263, and 202, CL = 2.5 for 335 and 265 with the outputs open.
9. Enables on-chip refresh and address counters.
10. I_{DD} specifications are tested after the device is properly initialized, and is averaged at the defined cycle rate.
11. This parameter is sampled. V_{CC} = +2.5V ±0.2V, V_{CCQ} = +2.5V ±0.2V, V_{REF} = V_{SS}, f = 100 MHz, = 25°C, V_{OUT}(DC) = $V_{CCQ/2}$, V_{OUT} (peak to peak) T_A = 0.2V. DM input is grouped with I/O pins, reflecting the fact that they are matched in loading.
12. For slew rates less than 1 V/ns and greater than or equal to 0.5 V/ns. If slew rate is less than 0.5 V/ns, timing must be derated: t_{IS} has an additional 50ps per each 100mV/ns reduction in slew rate from 500mV/ns, while t_{IH} is unaffected. If slew rate exceeds 4.5 V/ns, functionality is uncertain. For 335, slew rates must be ≥ 0.5 V/ns.
13. The CK/CK# input reference level (for timing referenced to CK/CK#) is the point at which CK and CK# cross; the input reference level for signals other than CK/CK# is V_{REF}.
14. Inputs are not recognized as valid until V_{REF} stabilizes. Exception: during the period before V_{REF} stabilizes, CKE < 0.3 x V_{CCQ} is recognized as LOW.
15. The output timing reference level, as measured at the timing reference point indicated in Note 3, is V_{TT}.
16. t_{HZ} and t_{LZ} transitions occur in the same access time windows as valid data transitions. These parameters are not referenced to a specific voltage level, but specify when the device output is no longer driving (HZ) or begins driving (LZ).
17. The intent of the Don't Care state after completion of the postamble is the DQS-driven signal should either be high, low, or high-Z and that any signal transition within the input switching region must follow valid input requirements. That is, if DQS transitions high (above V_{IH} DC (MIN) then it must not transition low (below V_{IH} DC) prior to t_{DQSH} (MIN).
18. This is not a device limit. The device will operate with a negative value, but system performance could be degraded due to bus turnaround.
19. It is recommended that DQS be valid (HIGH or LOW) on or before the WRITE command. The case shown (DQS going from High-Z to logic LOW) applies when no WRITEs were previously in progress on the bus. If a previous WRITE was in progress, DQS could be HIGH during this time, depending on t_{DQSS}.
20. MIN (t_{RC} or t_{RFC}) for I_{DD} measurements is the smallest multiple of t_{CK} that meets the minimum absolute Value for the respective parameter. t_{RAS} (MAX) for I_{DD} measurements is the largest multiple of t_{CK} that meets the maximum absolute value for t_{RAS}.
21. The refresh period 64ms. This equates to an aver-age refresh rate of 7.8125µs. However, an AUTO REFRESH command must be asserted at least once every 70.3µs; burst refreshing or posting by the DRAM controller greater than eight refresh cycles is not allowed.
22. The valid data window is derived by achieving other specifications: t_{HP} ($t_{CK/2}$), t_{DQSQ}, and t_{QH} (t_{QH} = t_{HP} - t_{QHS}). The data valid window derates directly porportional with the clock duty cycle and a practical data valid window can be derived. The clock is allowed a maximum duty cycle variation of 45/55, beyond which functionality is uncertain. Figure 8, Derating Data Valid Window, shows derating curves for duty cycles ranging between 50/50 and 45/55.
23. Each byte lane has a corresponding DQS.
24. This limit is actually a nominal value and does not result in a fail value. CKE is HIGH during REFRESH command period (t_{RFC} [MIN]) else CKE is LOW (i.e., during standby).
25. To maintain a valid level, the transitioning edge of the input must:
    a. Sustain a constant slew rate from the current AC level through to the target AC level, V_{IL}(AC) or V_{IH}(AC).
    b. Reach at least the target AC level.After the AC target level is reached, continue to maintain at least the target DC level, V_{IL}(DC) or V_{IH}(DC).
26. JEDEC specifies CK and CK# input slew rate must be ≥ 1V/ns (2V/ns differentially).
27. DQ and DM input slew rates must not deviate from DQS by more than 10 percent. If the DQ/ DM/DQS slew rate is less than 0.5V/ns, timing must be derated: 50ps must be added to t_{DS} and t_{DH} for each 100mv/ns reduction in slew rate. If slew rate exceeds 4V/ns, functionality is uncertain. For 335, slew rates must be ≥ 0.5 V/ns.
28. V_{CC} must not vary more than 4 percent if CKE is not active while any bank is active.
29. The clock is allowed up to ±150ps of jitter. Each timing parameter is allowed to vary by the same amount.
30. t_{HP} min is the lesser of t_{CL} minimum and t_{CH} minimum actually applied to the device CK and CK# inputs, collectively during bank active.
31. READs and WRITEs with auto precharge are not allowed to be issued until t_{RAS}(MIN) can be satisfied prior to the internal precharge command being issued.
32. Any positive glitch must be less than 1/3 of the clock and not more than +400mV or 2.9V, whichever is less. Any negative glitch must be less than 1/3 of the clock cycle and not exceed either -300mV or 2.2V, whichever is more positive.

White Electronic Designs Corp. reserves the right to change products or specifications without notice.

33. The voltage levels used are derived from a mini-mum V_{CC} level and the referenced test load. In practice, the voltage levels obtained from a properly terminated bus will provide significantly different voltage values.
34. V_{IH} overshoot: V_{IH} (MAX) = V_{CCQ} + 1.5V for a pulse width ≤ 3ns and the pulse width can not be greater than 1/3 of the cycle rate. V_{IL} undershoot: V_{IL} (MIN) = -1.5V for a pulse width ≤ 3ns and the pulse width can not be greater than 1/3 of the cycle rate.
35. V_{CC} and V_{CCQ} must track each other.
36. t_{HZ} (MAX) will prevail over t_{DQSCK} (MAX) + t_{RPST} (MAX) condition. t_{LZ} (MIN) will prevail over t_{DQSCK} (MIN) + t_{RPRE} (MAX) condition.
37. t_{RPST} end point and t_{RPRE} begin point are not referenced to a specific voltage level but specify when the device output is no longer driving (t_{RPST}), or begins driving (t_{RPRE}).
38. During Initialization, V_{CCQ}, V_{TT}, and V_{REF} must be equal to or less than V_{CC} + 0.3V. Alternatively, V_{TT} may be 1.35V maximum during power up, even if V_{CC}/V_{CCQ} are 0.0V, provided a minimum of 42 0 of series resistance is used between the V_{TT} supply and the input pin.
39. The current part operates below the slowest JEDEC operating frequency of 83 MHz. As such, future die may not reflect this option.
40. Random addressing changing and 50 percent of data changing at every transfer.
41. Random addressing changing and 100 percent of data changing at every transfer.
42. CKE must be active (high) during the entire time a refresh command is executed. That is, from the time the AUTO REFRESH command is registered, CKE must be active at each rising clock edge, until tREF later.
43. I_{DD2N} specifies the DQ, DQS, and DM to be driven to a valid high or low logic level. I_{DD2Q} is similar to I_{DD2F} except I_{DD2Q} specifies the address and control inputs to remain stable. Although I_{DD2F}, I_{DD2N}, and I_{DD2Q} are similar, I_{DD2F} is "worst case."
44. Whenever the operating frequency is altered, not including jitter, the DLL is required to be reset. This is followed by 200 clock cycles.
45. Leakage number reflects the worst case leakage possible through the module pin, not what each memory device contributes.
46. When an input signal is HIGH or LOW, it is defined as a steady state logic HIGH or LOW.
47. The 335 speed grade will operate with t_{RAS} (MIN) = 40ns and t_{RAS} (MAX) = 120,000ns at any slower frequency.

White Electronic Designs Corp. reserves the right to change products or specifications without notice.

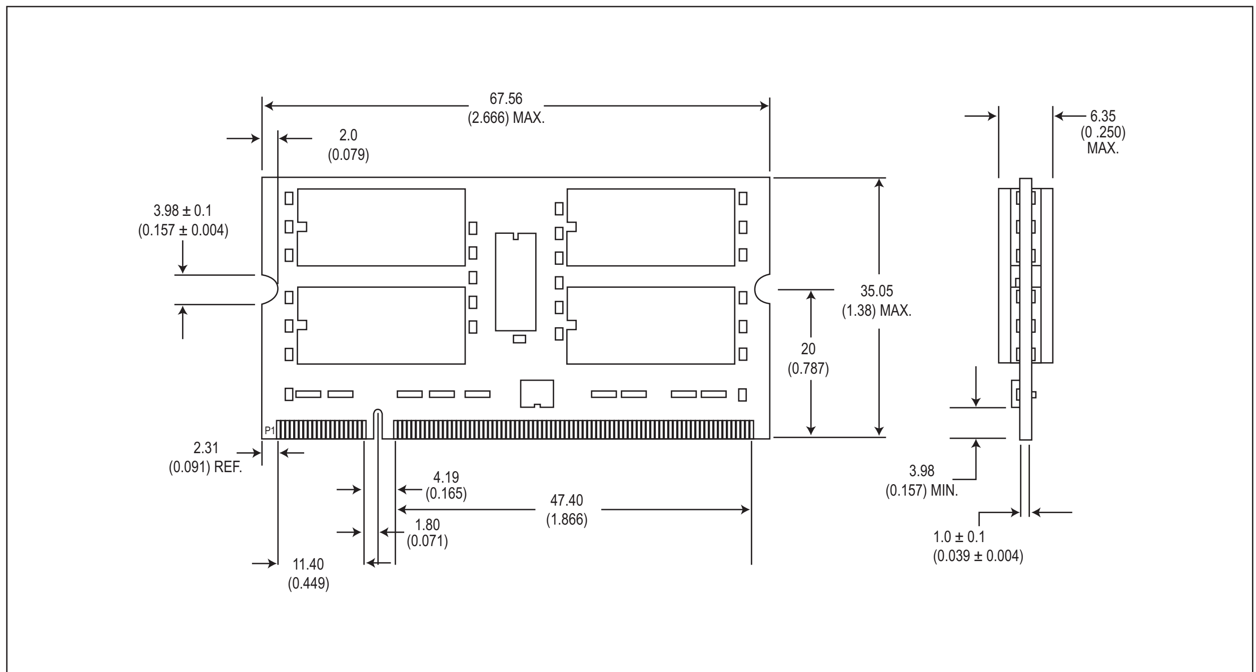
ORDERING INFORMATION FOR AD4

Part Number	Speed	Height*
W3EG6466S335AD4	166MHz/333Mbps, CL=2.5	35.5 (1.38)
W3EG6466S262AD4	133MHz/266Mbps, CL=2	35.5 (1.38)
W3EG6466S265AD4	133MHz/266Mbps, CL=2.5	35.5 (1.38)
W3EG6466S202AD4	100MHz/200Mbps, CL=2	35.5 (1.38)

NOTES:

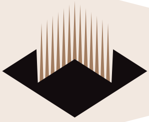
- Consult Factory for availability of RoHS compliant products. (G = RoHS Compliant)
- Vendor specific part numbers are used to provide memory components source control. The place holder for this is shown as lower case “x” in the part numbers above and is to be replaced with the respective vendors code. Consult factory for qualified sourcing options. (M = Micron, S = Samsung & consult factory for others)
- Consult factory for availability of industrial temperature (-40°C to 85°C) option

PACKAGE DIMENSIONS FOR AD4



* ALL DIMENSIONS ARE IN MILIMETERS AND (INCHES)

White Electronic Designs Corp. reserves the right to change products or specifications without notice.



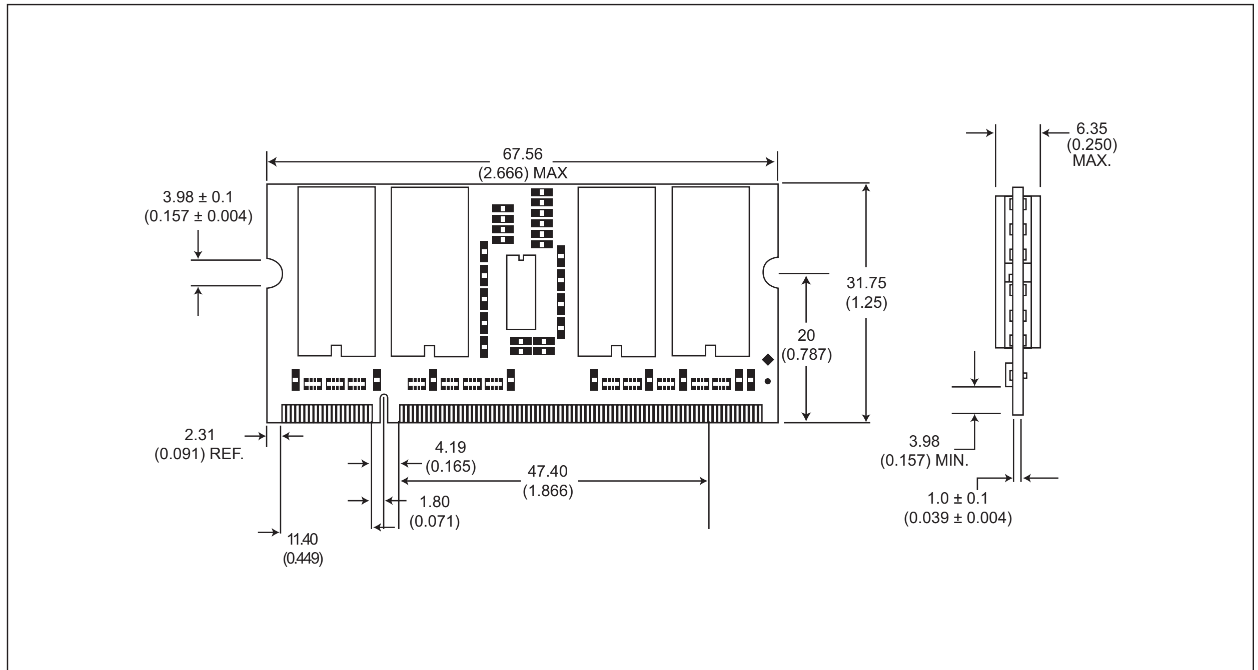
ORDERING INFORMATION FOR BD4

Part Number	Speed	Height*
W3EG6466S335BD4	166MHz/333Mbps, CL=2.5	31.75 (1.25)
W3EG6466S262BD4	133MHz/266Mbps, CL=2	31.75 (1.25)
W3EG6466S265BD4	133MHz/266Mbps, CL=2.5	31.75 (1.25)
W3EG6466S202BD4	100MHz/200Mbps, CL=2	31.75 (1.25)

NOTES:

- Consult Factory for availability of RoHS compliant products. (G = RoHS Compliant)
- Vendor specific part numbers are used to provide memory components source control. The place holder for this is shown as lower case "x" in the part numbers above and is to be replaced with the respective vendors code. Consult factory for qualified sourcing options. (M = Micron, S = Samsung & consult factory for others)
- Consult factory for availability of industrial temperature (-40°C to 85°C) option

PACKAGE DIMENSIONS FOR BD4



* ALL DIMENSIONS ARE IN MILIMETERS AND (INCHES)

Document Title

512MB – 64Mx64 DDR SDRAM UNBUFFERED, w/PLL

Revision History

Rev #	History	Release Date	Status
Rev A	Created	7-21-02	Advanced
Rev 0	0.1 Upated I_{DD} specs. 0.2 Added AD4 and BD4 package options 0.3 Added document title page 0.4 Removed "ED" from part number 0.5 Moved from advanced to preliminary	8-04	Preliminary
Rev 1	1.0 Upated I_{DD} and CAP specs. 1.1 Added AC specs	11-04	Preliminary
Rev 2	2.1 Added lead-free and RoHS notes 2.2 Added source control notes 2.3 Added industrial temperature options	1-05	Preliminary